

Benjamin Nachman

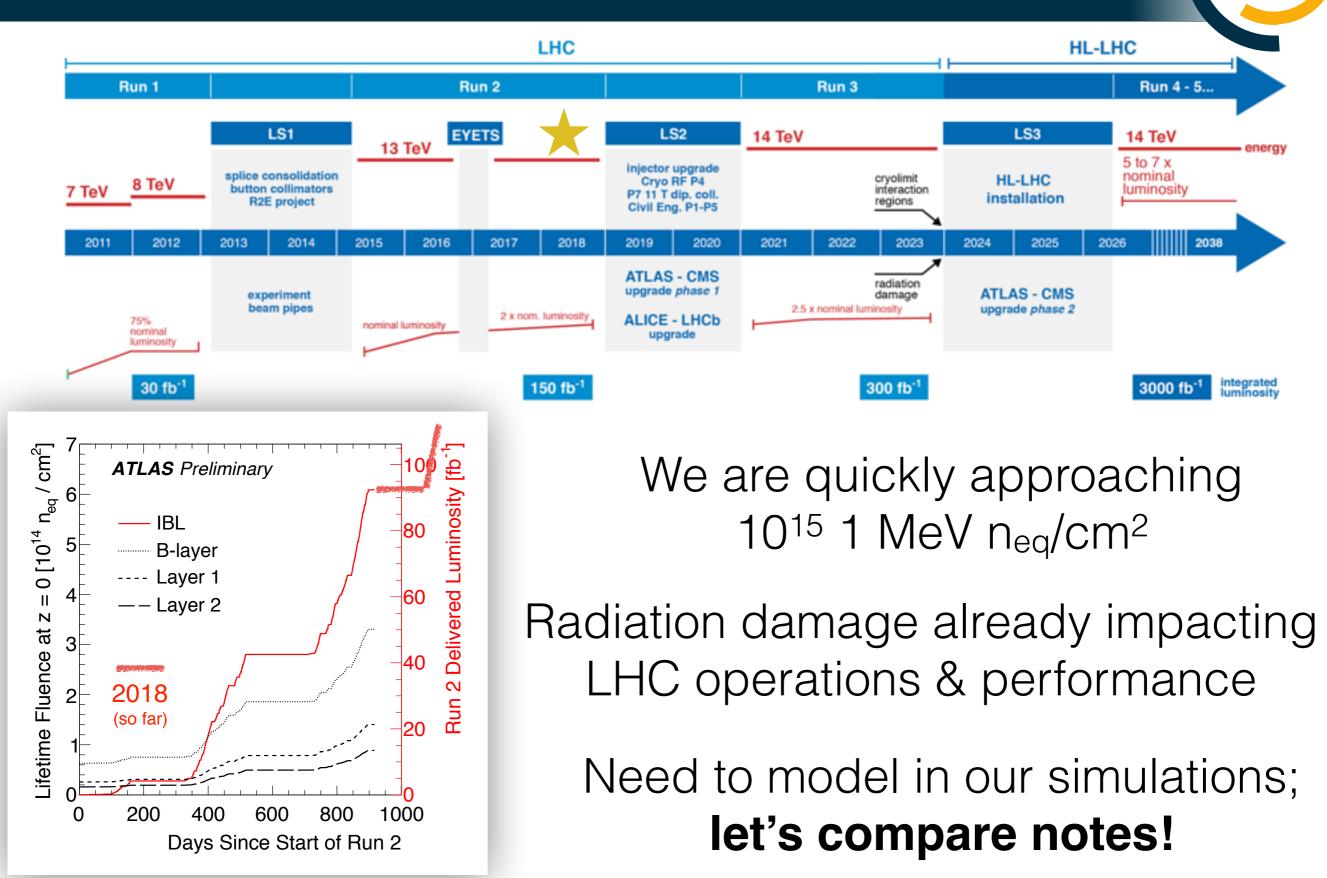
Lawrence Berkeley National Laboratory

June 2018 RD50 Workshop

on behalf of the recent LHC workshop participants



Motivation



Workshop Session Overview

14:00









	6-2-024 - BE Auditorium Meyrin, CERN		12:30 - 14:00
	Introduction		
	6-2-024 - BE Auditorium Meyrin, CERN		14:00 - 14:10
	Silicon Sensor Simulation in the ATLAS Monte Carlo Framework (2	20'+10') Bei	n Nachman 🥝
	6-2-024 - BE Auditorium Meyrin, CERN	<u>Ben Nachman</u>	14:10 - 14:40
Constant of the	Silicon Sensor Simulation in the LHCb Monte Carlo Framework (15	5'+5') Toma:	sz Szumlak 🥝
	6-2-024 - BE Auditorium Meyrin, CERN	<u>Tomasz Szumlak</u>	14:40 - 15:00
	Silicon Sensor Simulation in the CMS Monte Carlo Framework (15'	Morris Swartz	Swartz et al. 🥝
	6-2-024 - BE Auditorium Meyrin, CERN	IVIORIS Swartz	15:00 - 15:20
	Coffee break		
	6-2-024 - BE Auditorium Meyrin, CERN		15:20 - 15:50
1	Cluster and Track Property Data/MC in ATLAS (20'+5')		nzo Rossini 🥝
	6-2-024 - BE Auditorium Meyrin, CERN	<u>_orenzo Rossini</u>	15:50 - 16:15
	Discussion and Closeout		

17:00

Monte Carlo Simulation

LEILELLELL m mmm and a constant and a mmmmm Recence Spanning 10⁻²⁰ m up to 1 m can take O(min/event) Inspired by Sherpa 1.1 paper

Monte Carlo Simulation

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Hard-scatter

MadGraph 5 / aMC@NLO POWHEG-BOX

Fragmentation

Pythia, Herwig, Sherpa

Material Interactions

Geant 4

this

talk

Digitization

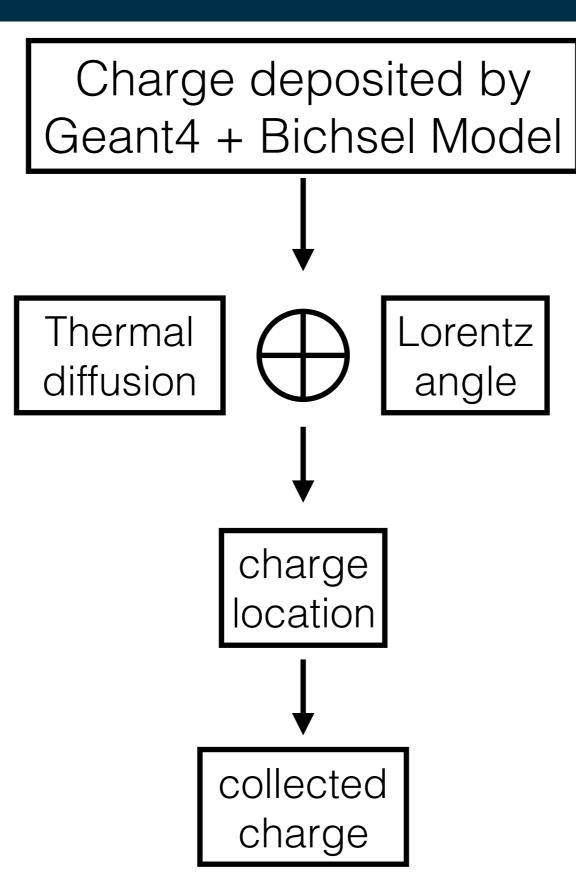
Inspired by Custom code Sherpa 1.1 paper

Current Run 2 (Si) Simulation 6 H **Bichsel Model** Energy Geant4 Geant4 Deposition + G4 (δ -rays) Energy from Bichsel from Uniform (space) + spreading uniform/Gauss (E) Geant4 + chunking E-field/ uniform uniform N/A Lorentz angle Diffusion Einstein Einstein tuned capacitive capacitive Noise not discussed coupling + noise coupling + noise Radiation none none none damage

Next Generation (Si) Simulation

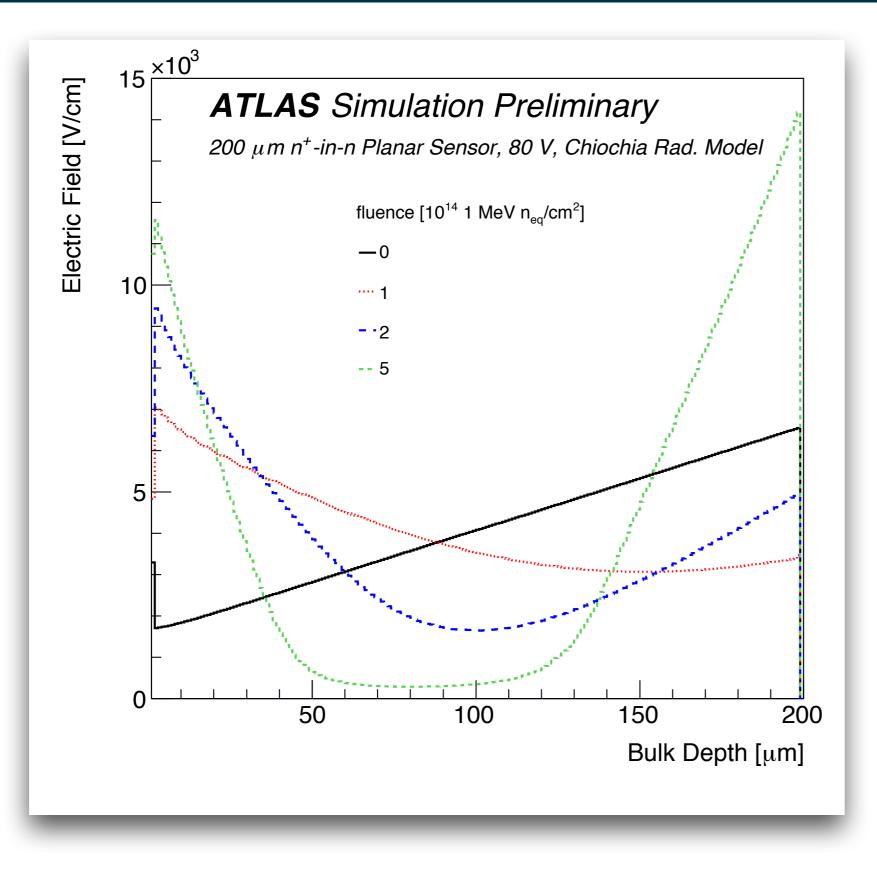
	ATLAS	CMS	LHCb THCp
Energy Deposition	Bichsel Model + G4 (δ-rays)	Pixelav (applied as correction to G4)	Geant4
Energy spreading	from Bichsel + chunking	from Bichsel + chunking	Uniform (space) + uniform/Gauss (E)
E-field/ Lorentz angle	TCAD (<u>Chiochia et al.</u>)	TCAD (tuned to data)	N/A
Diffusion	Einstein	Einstein	tuned
Noise	capacitive coupling + noise	not discussed	capacitive coupling + noise
Radiation damage	trapping + charge induction	trapping + charge induction	charge & 'diffusion' corrections

Current ATLAS Pixel Simulation



New ATLAS Pixel Simulation 9 Charge deposited by fluence Geant4 + Bichsel Model trapping constant Thermal Lorentz diffusion angle time E-field travelled charge location (relies heavily on final lookup tables) depth Ramo per condition potential per geometry induced charge per e/h See talk at last RD50 meeting

TCAD in ATLAS

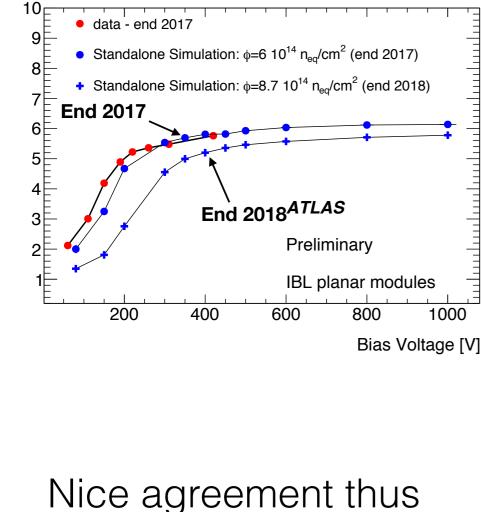


Silvaco TCAD with the radiation damage model from <u>Chiochia et al.</u>

> Parameters linearly interpolated when applicable.

Systematic uncertainty from varying parameters by ~10%; plan to tune/ constrain with data in the near future.

Validation with data

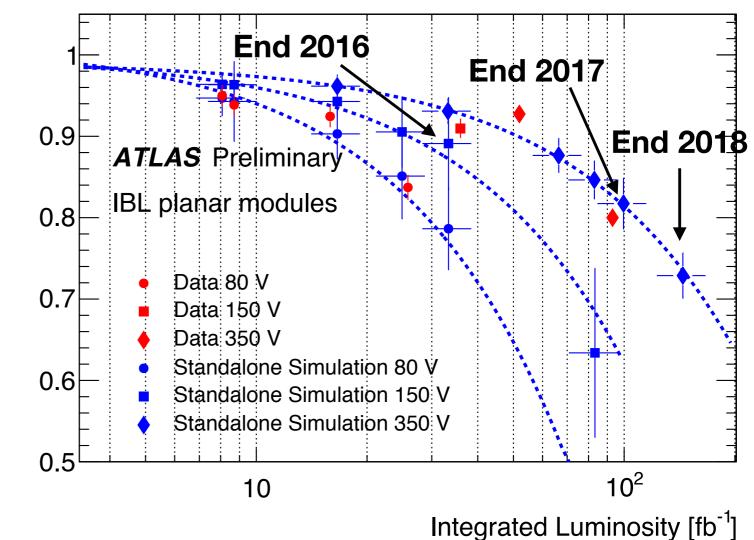


ToT [BC]

far, but large uncertainties - need to bring these down to make precise predictions!

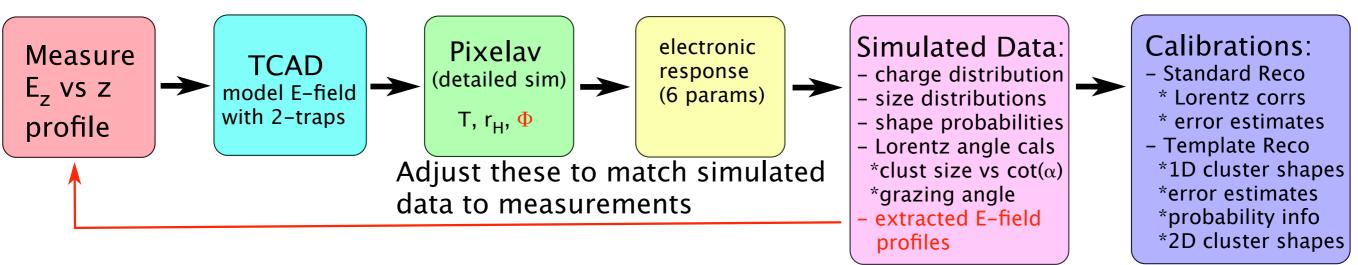


Measure and predict the charge as a function of fluence / bias voltage



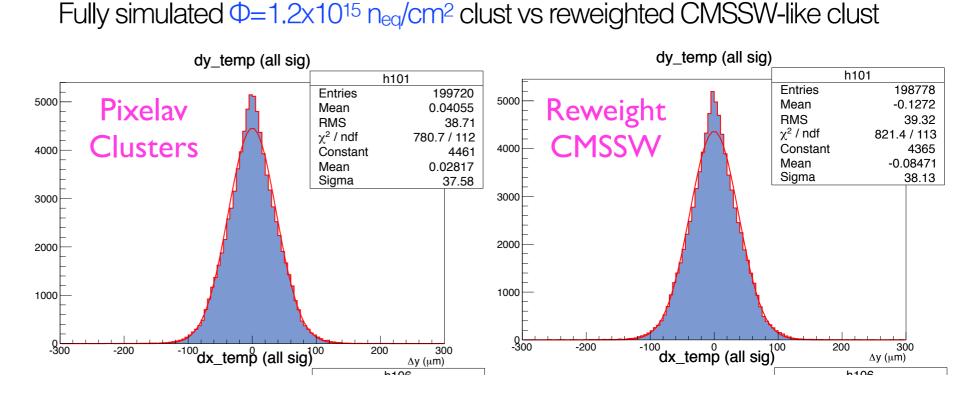
New CMS Pixel Simulation

The TCAD+Pixelav simulations are tuned to measured distributions



Different approach:

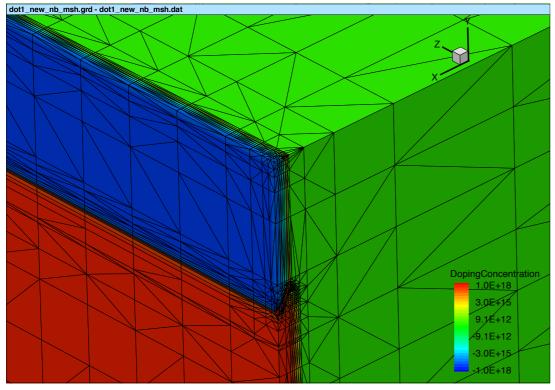
instead of modifying primary simulation, perform detailed independent simulation and apply correction factors.

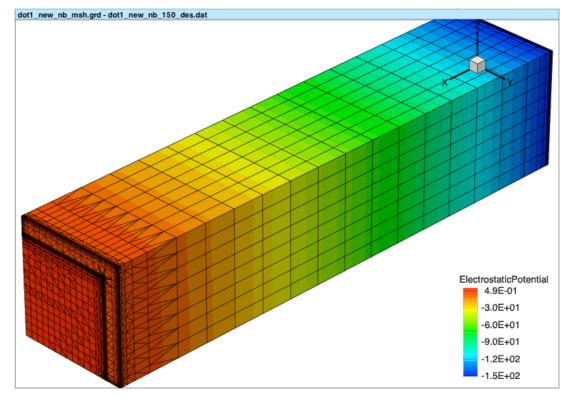


TCAD in CMS

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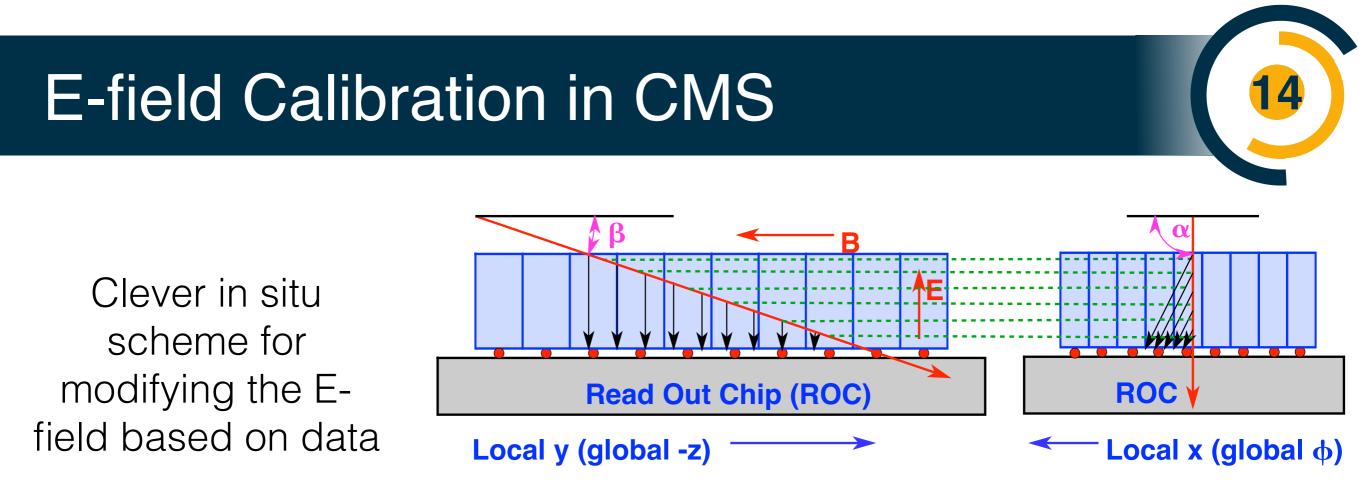
- Electric field calculation: uses TCAD 9.0 software
 - simultaneously solves Poisson and carrier continuity eqs
 - includes lots of semiconductor physics (including SRH)
 - simulate 1/4 (1/2) pixel cell to keep mesh size ~17000 (25000) nodes. This requires 4-fold (2-fold) symmetry.
 - no process simulation, use MESH w/ analytic doping profiles to generate grid and doping files

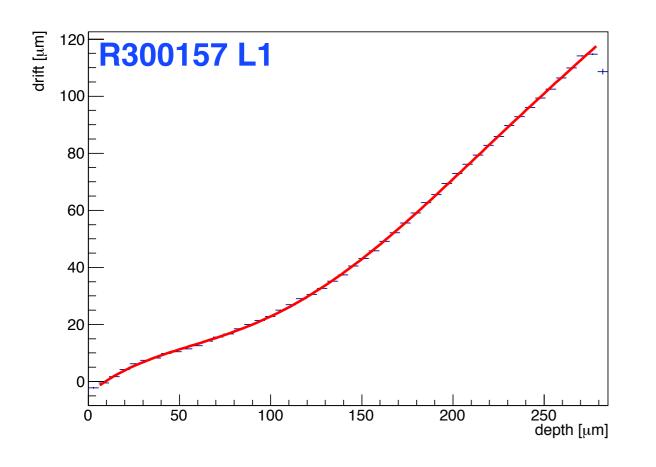




doping profiles

potential distribution

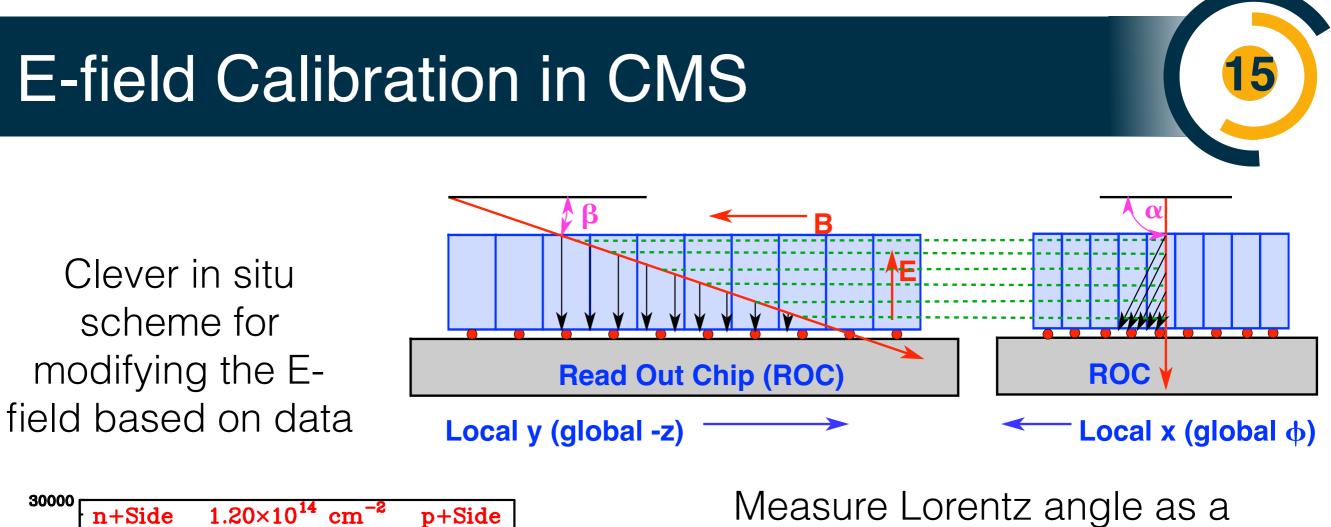


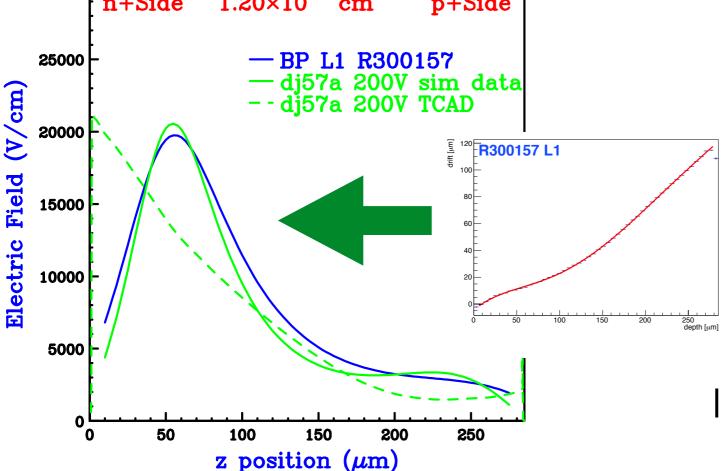


Measure Lorentz angle as a function of length inside long cluster (probes depth)

$$\tan \theta_L = \frac{dx}{dD} = r_H \mu(E) B_y$$
$$\rightarrow E = \mu^{-1} \left(\frac{1}{r_H B_y} \frac{dx}{dD} \right)$$

Independent of trapping; tune the trap densities to match data.



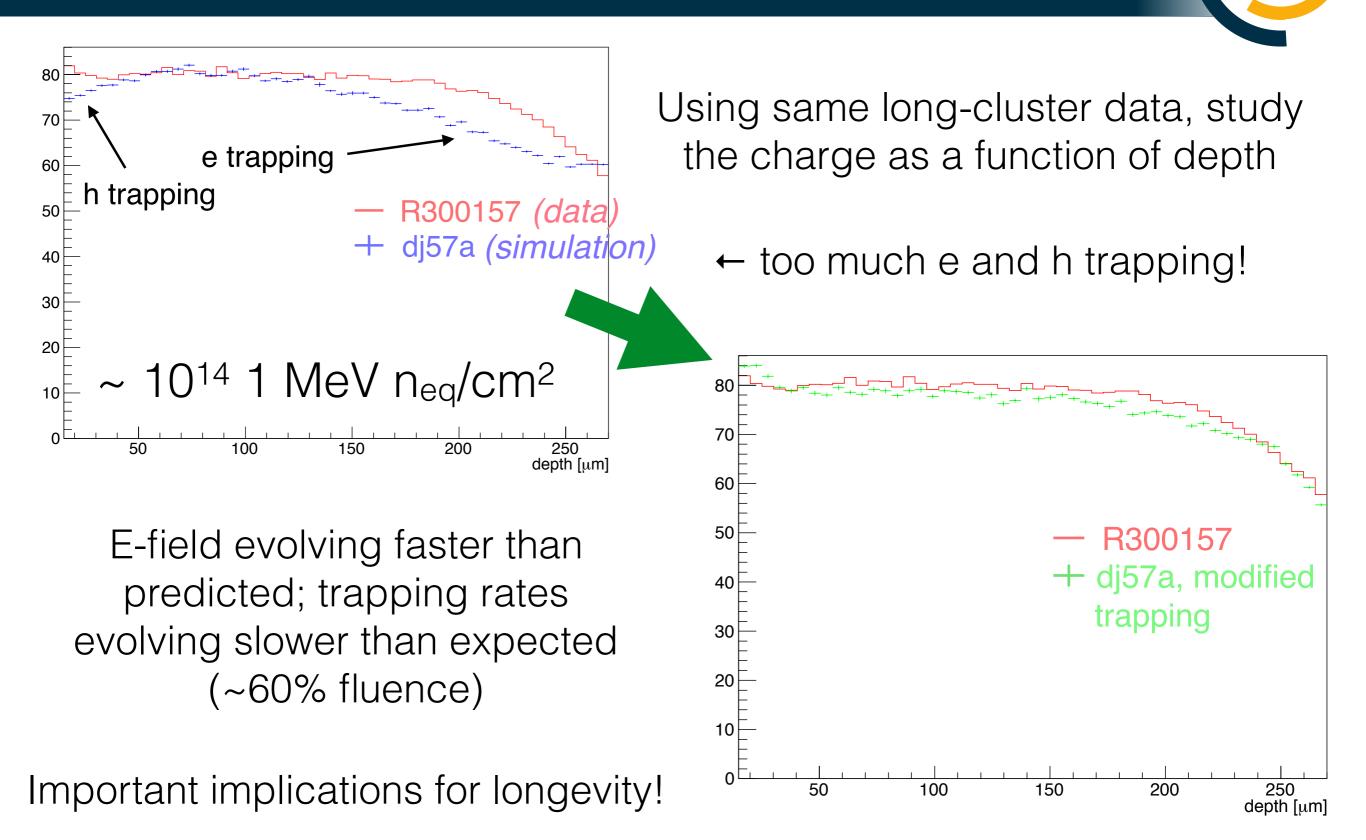


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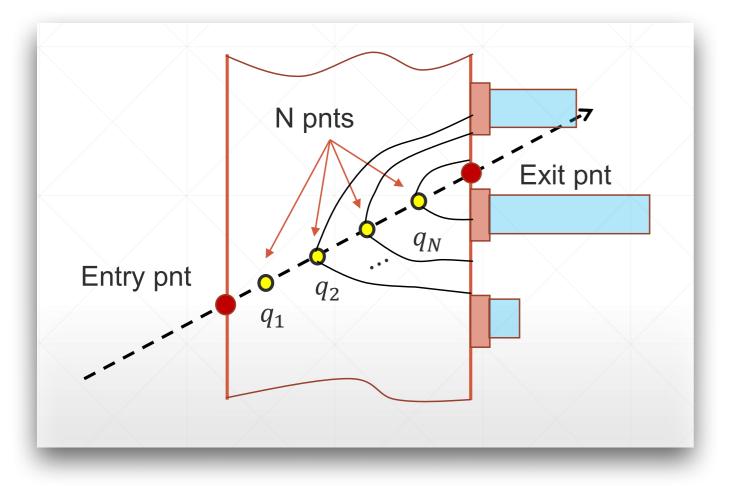
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Independent of trapping; tune the trap densities to match data.

Trapping Calibration in CMS



New LHCb Pixel Simulation



Different than both ATLAS/ CMS: reduce charge and increase "diffusion length" to match data.

Tuned once/year.

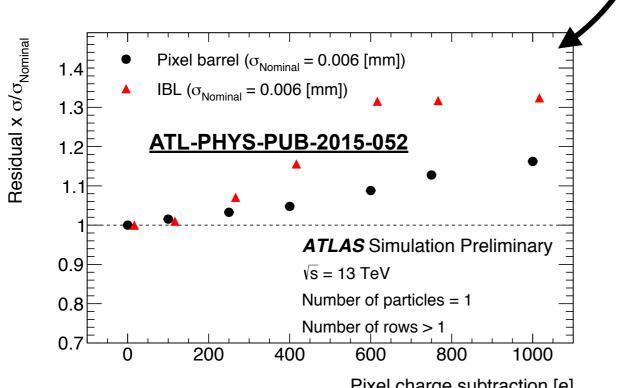
Preliminary results look promising and validation with bigger simulations is ongoing.

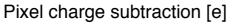
Impact on Physics and Performance

Charge loss directly effects searches for new highly ionizing particles →

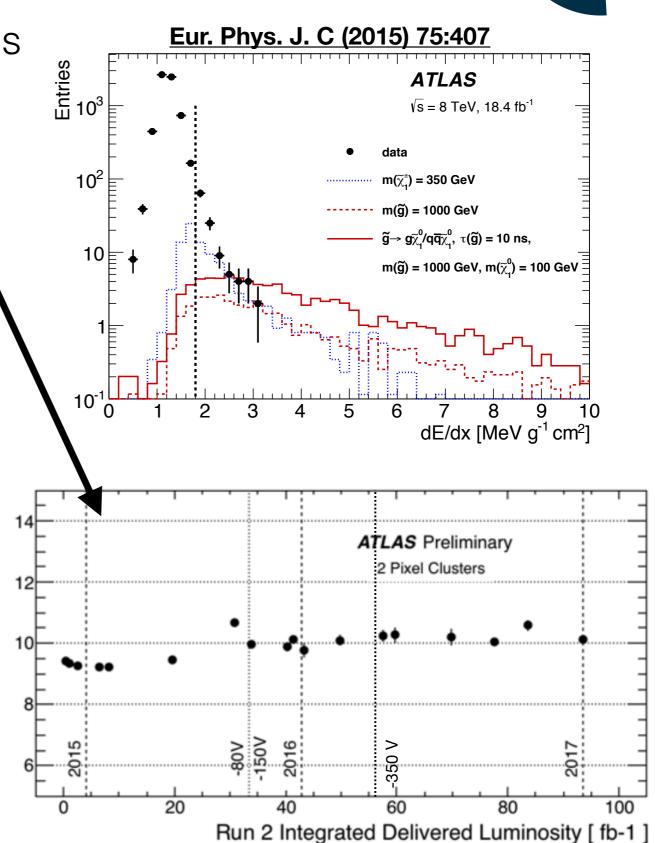
We may be seeing a degradation in position resolution.

Widespread loss in performance not yet, but **inevitable** - we must continue to monitor and model!





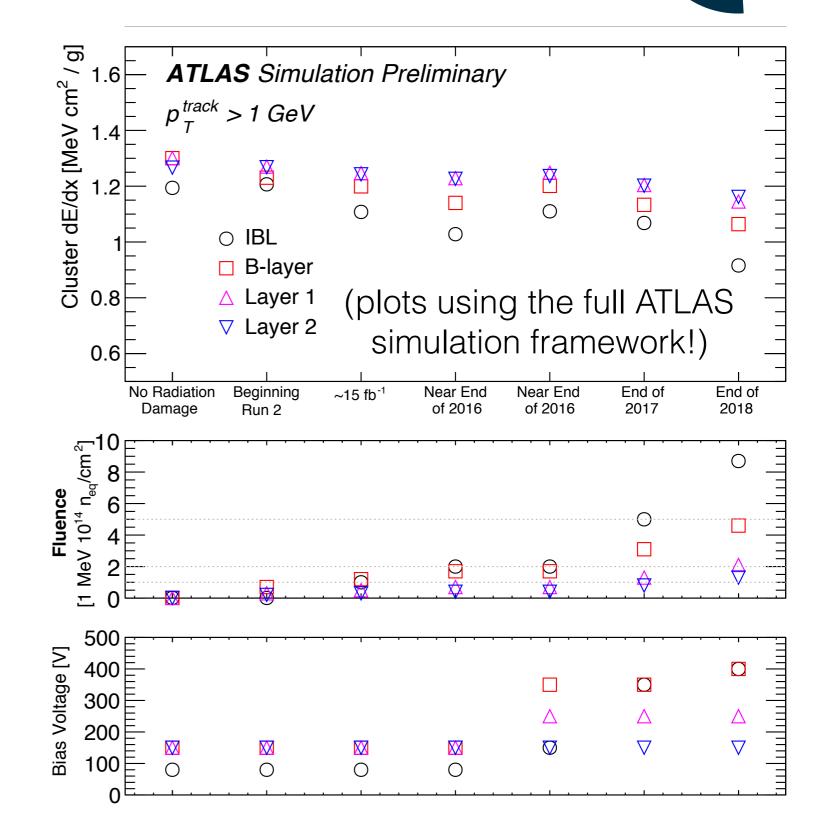
BL Overlap r-φ Resolution [μm]



Plans for the future

ATLAS, CMS, and LHCb are planning to incorporate radiation damage into their main simulation.

All three approaches are different and it will be very valuable to continue to compare notes as we accurate more experience with more data (=damage)



Conclusions





Looking forward to the next gathering after we have the full Run 2 dataset!

*for our **default** simulation and for radiation damage The inter-experiment workshop was an excellent opportunity to gather experts and exchange our methods and ideas*

